

What Is Claimed Is:



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 1. An electroluminescent device comprising:

a substrate;

a lower electrode layer over the substrate, having a plurality of convex shapes in its surface;

an insulating layer over the lower electrode layer;

a light-emitting layer over the insulating layer;

an upper electrode layer over the light-emitting layer; and

a passivation layer over the upper electrode layer,

wherein the insulating layer, the light-emitting layer, and the upper electrode layer are formed in succession.

- 2. The electroluminescent device according to claim 1, wherein the lower electrode layer has a layered structure including a polysilicon layer and a metal layer.
- 3. The electroluminescent device according to claim 2, wherein the polysilicon layer has a plurality of convex shapes in its surface.
- 4. The electroluminescent device according to claim 2, wherein the metal layer includes at least one of Al and Ag.

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- The electroluminescent device according to claim 1, wherein the lower electrode 5. layer has a layered structure including a tungsten layer and a metal layer.
- 6. The electroluminescent device according to claim 5, wherein the tungsten layer has a plurality of convex shapes in its surface.
- The electroluminescent device according to claim 5, wherein the metal layer 7. includes at least one of Al and Ag.
- The electroluminescent device according to claim 1, wherein the insulating layer, 8. the light-emitting layer, and the upper electrode layer have substantially the same surface profile as the lower electrode layer.
- The electroluminescent device according to claim 1, wherein the lower electrode 9. layer has a single layer structure of a metal layer.
- The electroluminescent device according to claim 9, wherein the metal layer 10. includes at least one of Al and Ag.
- The electroluminescent device according to claim 1, wherein the insulating layer 11. includes BaTiO₃.

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- 12. The electroluminescent device according to claim 1, wherein the upper electrode layer includes indium tin oxide (ITO).
- 13. The electroluminescent device according to claim 1, wherein the light-emitting layer includes ZnS doped with at least one of Cu and Ma.

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A method for manufacturing an electroluminescent device, the method 14. comprising:

forming, over a substrate, a lower electrode layer having a plurality of convex shapes in its surface;

forming, over the lower electrode layer, an insulating layer, a light-emitting layer, and an upper electrode layer in succession so that the insulating layer, the light-emitting layer, and the upper electrode layer have substantially the same surface profile as the lower electrode layer; and forming a passivation layer over the upper electrode layer.

The method according to claim 14, wherein forming the lower electrode layer 15. includes:

forming, over the substrate, a polysilicon layer having a plurality of convex shapes in its surface; and

forming, over the polysilicon layer, a metal layer having substantially the same surface profile as the polysilicon layer.

- The method according to claim 15, wherein the polysilicon layer is formed by low 16. pressure chemical vapor deposition (LPCVD) at a temperature between about 560°C and about 610°C.
- The method according to claim 14, wherein forming the lower electrode layer 17. includes:

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forming, over the substrate, a tungsten layer having a plurality of convex shapes in its surface; and

forming, over the tungsten layer, a metal layer having substantially the same surface profile as the tungsten layer.

- 18. The method according to claim 17, wherein the tungsten layer is formed by chemical vapor deposition (CVD).
- 19. The method according to claim 14, wherein forming the lower electrode layer includes:

forming a metal layer over the substrate; and etching a surface of the metal layer to form a plurality of convex shapes thereon.

- 20. The method according to claim 19, wherein the metal layer is formed by thermal deposition.
- 21. The method according to claim 19, wherein etching the surface of the metal layer includes performing at least one of wet etching and dry etching.
- 22. The method according to claim 14, wherein forming the insulating layer includes forming a BaTiO₃ based material.

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- The method according to claim 14, wherein forming the light-emitting layer 23. includes performing at least one of electron beam deposition and sputtering.
- The method according to claim 14, wherein forming the upper electrode layer 24. includes;

forming an indium tin oxide (ITO) layer; and patterning the indium thin oxide layer.

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25. An electroluminescent device comprising:

a substrate;

a lower electrode layer over the substrate, having an uneven surface profile;
an insulating layer over the lower electrode layer, having an uneven surface profile substantially corresponding to the uneven surface profile of the lower electrode layer;

a light-emitting layer over the insulating layer, having an uneven surface profile substantially corresponding to the uneven surface profile of the insulating layer; and

an upper electrode layer over the light-emitting layer, having an uneven surface profile substantially corresponding to the uneven surface profile of the light-emitting layer.

26. The electroluminescent device according to claim 1, wherein the uneven surface profile of the lower electrode has a plurality of convex shapes each of which is substantially hemispheric.

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